

ABSTRACT OF THE DISCLOSURE

There is provided a semiconductor device comprising a dielectric film made of a high dielectric constant material, in which
5 a leak current is reduced in the film and which exhibits improved device reliability. Specifically, a dielectric film 142 is a metal-compound film having a composition represented by the formula $MO_xC_yN_z$ wherein x, y and z meet the conditions: $0 < x$, $0.1 \leq y \leq 1.25$, $0.01 \leq z$ and $x+y+z=2$; and M comprises at least Hf or Zr.